

製品概要

FFSP3065B-F085: Automotive Silicon Carbide (SiC) Schottky Diode, 650 V

技術情報は、データシートをご参照ください。

Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size & cost

特長

- Max Junction Temperature 175°C
- Avalanche Rated 144 mJ
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery / No Forward Recovery
- AEC-Q101 Qualified and PPAP capable

利点

- $T_j = 175^\circ\text{C}$

アプリケーション

- Automotive HEV-EV Onboard Chargers
- Automotive HEV-EV DC-DC Converters

最終製品

- Automotive HEV-EV Onboard Chargers

電氣的仕様

製品	Pricing (\$/Unit)	Compliance	Status	Device Grade	Configuration	V_{RRM} (V)	$I_{F(ave)}$ (A)	V_F (Max)	I_{FSM} (A)	I_R (Max) (μA)	Package Type
FFSP3065B-F085	4.4799	AEC Qualified PPAP Capable Pb-free Halide free	Active	Automotive	Single	650	30	1.7	120	160	TO-220-2

詳細は、弊社 www.onsemi.jp の営業または販売代理店にお問い合わせください。

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